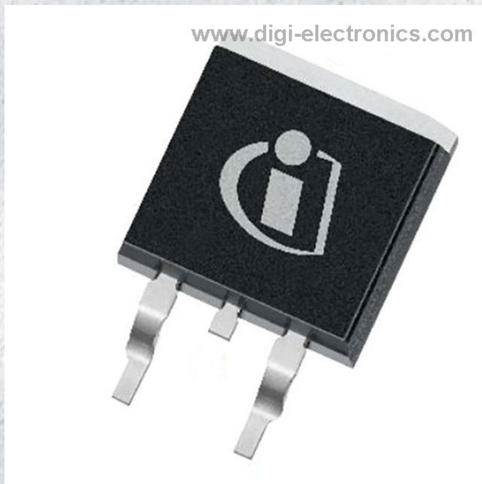
IPB043N10NF2SATMA1 Datasheet



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DiGi Electronics Part Number	IPB043N10NF2SATMA1-DG
Manufacturer	Infineon Technologies
Manufacturer Product Number	IPB043N10NF2SATMA1
Description	AUTOMOTIVE MOSFET
Detailed Description	N-Channel 100 V 21A (Ta), 135A (Tc) 3.8W (Ta), 167 W (Tc) Surface Mount PG-TO263-3

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Purchase and inquiry

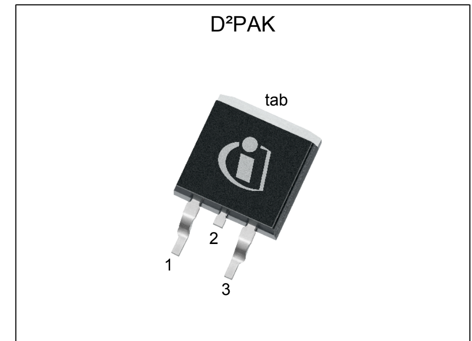
Manufacturer Product Number:	Manufacturer:
IPB043N10NF2SATMA1	Infineon Technologies
Series:	Product Status:
StrongIRFET™ 2	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
100 V	21A (Ta), 135A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
6V, 10V	4.35mOhm @ 80A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
3.8V @ 93µA	85 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	4000 pF @ 50 V
FET Feature:	Power Dissipation (Max):
-	3.8W (Ta), 167W (Tc)
Operating Temperature:	Mounting Type:
-55°C ~ 175°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
PG-TO263-3	TO-263-3, D2PAK (2 Leads + Tab), TO-263AB

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	

MOSFET

StrongIRFET™ 2 Power-Transistor



Features

- Optimized for a wide range of applications
- N-Channel, normal level
- 100% avalanche tested
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

Product validation

Qualified according to JEDEC Standard

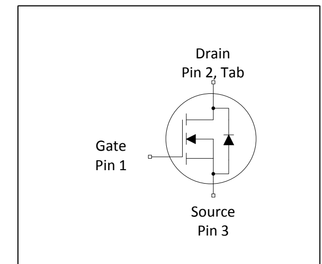


Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	100	V
$R_{DS(on),max}$	4.35	mΩ
I_D	135	A
Q_{oss}	74	nC
Q_G	57	nC

RoHS

Type / Ordering Code	Package	Marking	Related Links
IPB043N10NF2S	PG-TO263-3	043N10NS	-

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1 Maximum ratings

at T_A=25 °C, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current[1]	I_D	- - - -	- - - -	135 97 86 21	A	V_{GS}=10 V, T_C=25 °C V_{GS}=10 V, T_C=100 °C V_{GS}=6 V, T_C=100 °C V_{GS}=10V, T_A=25°C, R_{thJA}=40°C/W[2]
Pulsed drain current[3]	$I_{D,pulse}$	-	-	540	A	T_A=25 °C
Avalanche energy, single pulse[4]	E_{AS}	-	-	105	mJ	I_D=82 A, R_{GS}=25 Ω
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	- -	- -	167 3.8	W	T_C=25 °C T_A=25 °C, R_{thJA}=40 °C/W[2]
Operating and storage temperature	T_j, T_{stg}	-55	-	175	°C	-

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	0.9	°C/W	-
Thermal resistance, junction - ambient, 6 cm² cooling area[2]	R_{thJA}	-	-	40	°C/W	-
Thermal resistance, junction - ambient, minimal footprint	R_{thJA}	-	-	62	°C/W	-

[1] Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature as specified. For other case temperatures please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.
[2] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm^2 (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.
[3] See Diagram 3 for more detailed information
[4] See Diagram 13 for more detailed information

3 Electrical characteristics

at T_j=25 °C, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	100	-	-	V	V_{GS}=0 V, I_D=1 mA
Gate threshold voltage	$V_{GS(th)}$	2.2	3.0	3.8	V	V_{DS}=V_{GS}, I_D=93 µA
Zero gate voltage drain current	I_{DSS}	- -	0.1 10	1 100	µA	V_{DS}=100 V, V_{GS}=0 V, T_j=25 °C V_{DS}=100 V, V_{GS}=0 V, T_j=125 °C
Gate-source leakage current	I_{GSS}	-	10	100	nA	V_{GS}=20 V, V_{DS}=0 V
Drain-source on-state resistance	$R_{DS(on)}$	- -	3.8 4.6	4.35 5.6	mΩ	V_{GS}=10 V, I_D=80 A V_{GS}=6 V, I_D=40 A
Gate resistance	R_G	-	1.3	-	Ω	-
Transconductance[1]	g_{fs}	70	-	-	S	$\|V_{DS}\|\geq 2\|I_D\|R_{DS(on)max}$, I_D=80 A

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	4000	-	pF	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz
Output capacitance	C_{oss}	-	630	-	pF	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz
Reverse transfer capacitance	C_{rss}	-	28	-	pF	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz
Turn-on delay time	$t_{d(on)}$	-	18	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=80 A, $R_{G,ext}$=1.6 Ω
Rise time	t_r	-	71	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=80 A, $R_{G,ext}$=1.6 Ω
Turn-off delay time	$t_{d(off)}$	-	27	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=80 A, $R_{G,ext}$=1.6 Ω
Fall time	t_f	-	8	-	ns	V_{DD}=50 V, V_{GS}=10 V, I_D=80 A, $R_{G,ext}$=1.6 Ω

Table 6 Gate charge characteristics[2]

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	19	-	nC	V_{DD}=50 V, I_D=80 A, V_{GS}=0 to 10 V
Gate charge at threshold	$Q_{g(th)}$	-	12	-	nC	V_{DD}=50 V, I_D=80 A, V_{GS}=0 to 10 V
Gate to drain charge	Q_{gd}	-	12	-	nC	V_{DD}=50 V, I_D=80 A, V_{GS}=0 to 10 V
Switching charge	Q_{sw}	-	19	-	nC	V_{DD}=50 V, I_D=80 A, V_{GS}=0 to 10 V
Gate charge total[1]	Q_g	-	57	85	nC	V_{DD}=50 V, I_D=80 A, V_{GS}=0 to 10 V
Gate plateau voltage	$V_{plateau}$	-	4.8	-	V	V_{DD}=50 V, I_D=80 A, V_{GS}=0 to 10 V
Gate charge total, sync. FET	$Q_{g(sync)}$	-	49	-	nC	V_{DS}=0.1 V, V_{GS}=0 to 10 V
Output charge	Q_{oss}	-	74	-	nC	V_{DS}=50 V, V_{GS}=0 V

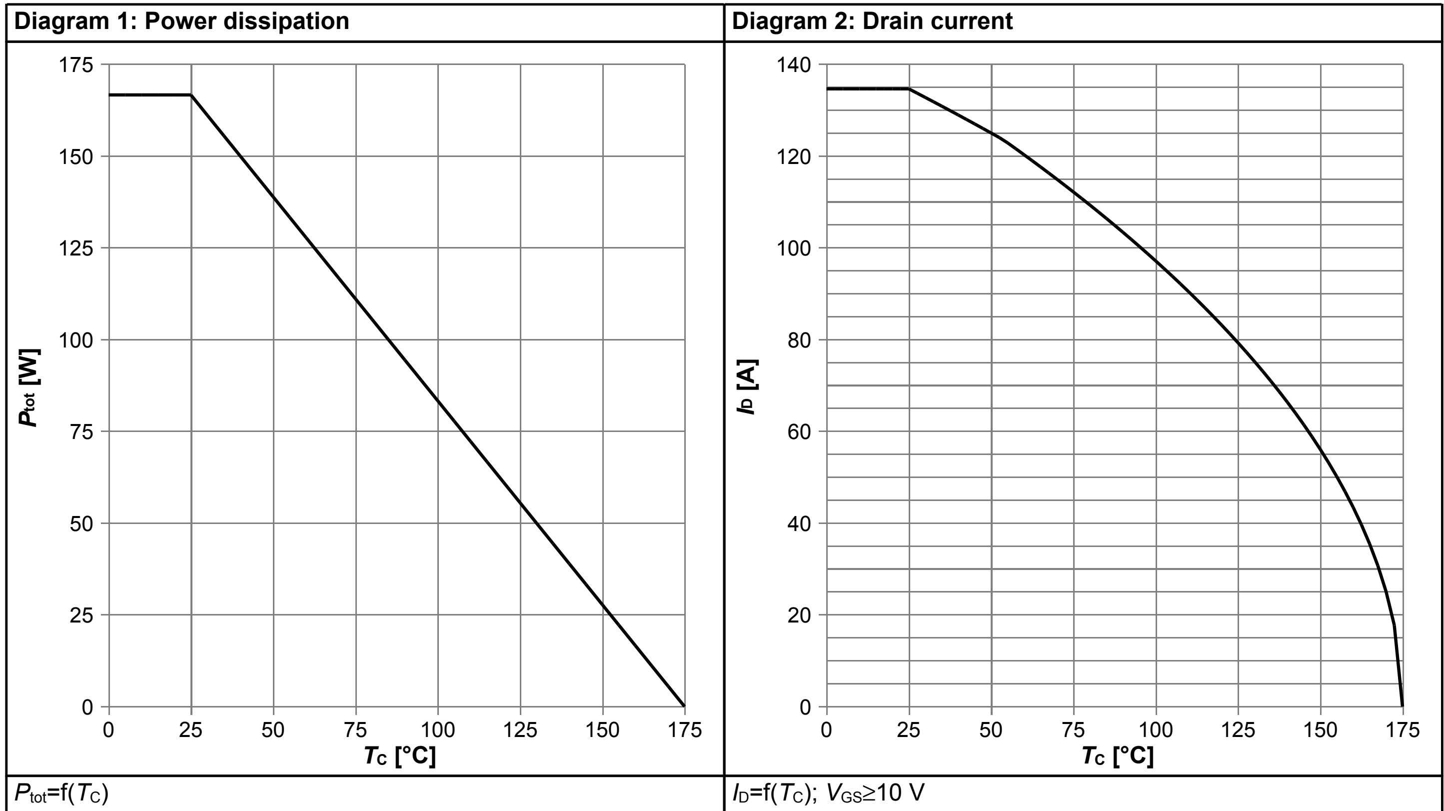
[1] Defined by design. Not subject to production test.
[2] See "Gate charge waveforms" for parameter definition

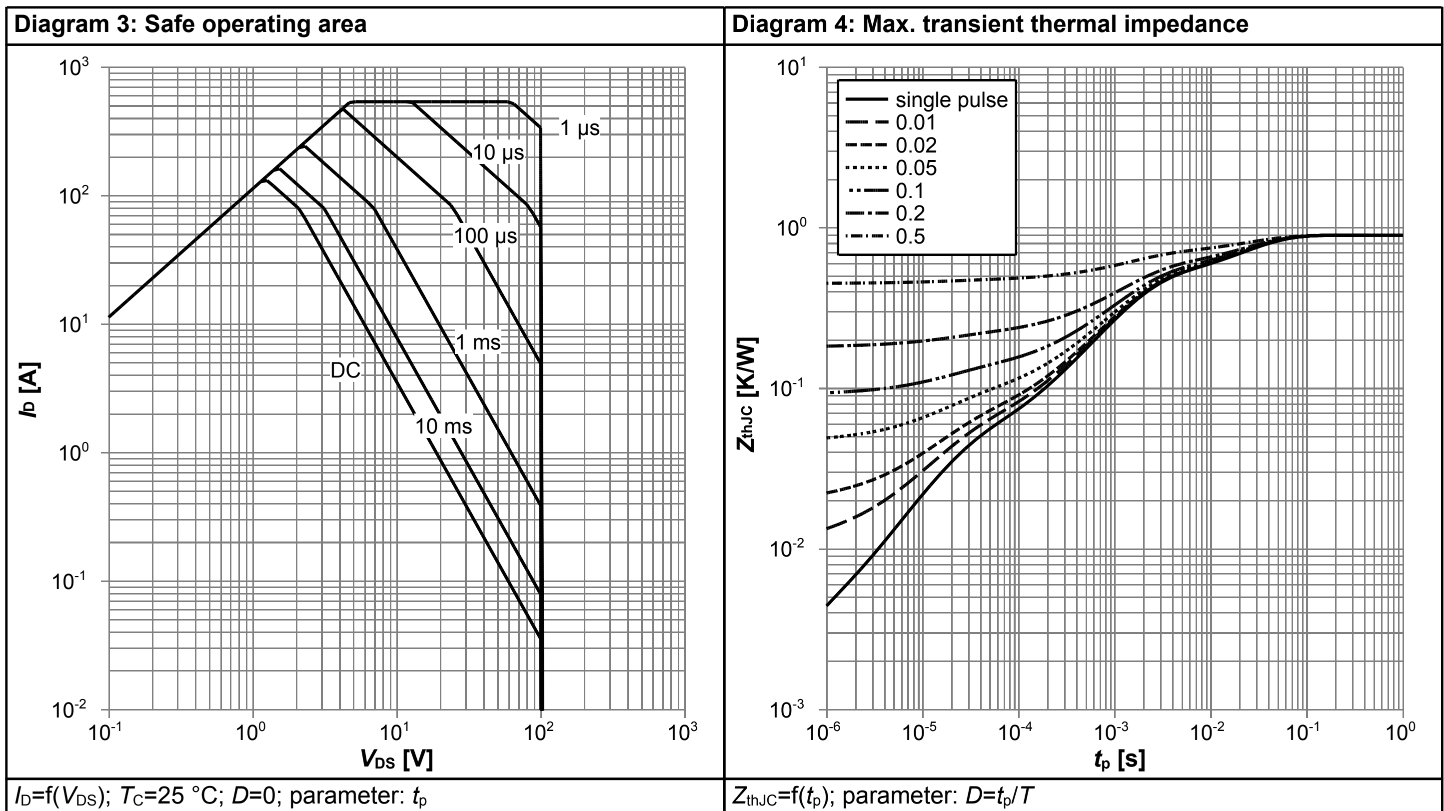
Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	123	A	T_C=25 °C
Diode pulse current	$I_{S,pulse}$	-	-	540	A	T_C=25 °C
Diode forward voltage	V_{SD}	-	0.92	1.2	V	V_{GS}=0 V, I_F=80 A, T_j=25 °C
Reverse recovery time	t_{rr}	-	40	-	ns	V_R=50 V, I_F=80 A, di_F/dt=500 A/µs
Reverse recovery charge	Q_{rr}	-	287	-	nC	V_R=50 V, I_F=80 A, di_F/dt=500 A/µs

StrongIRFET™ 2 Power-Transistor
IPB043N10NF2S

4 Electrical characteristics diagrams





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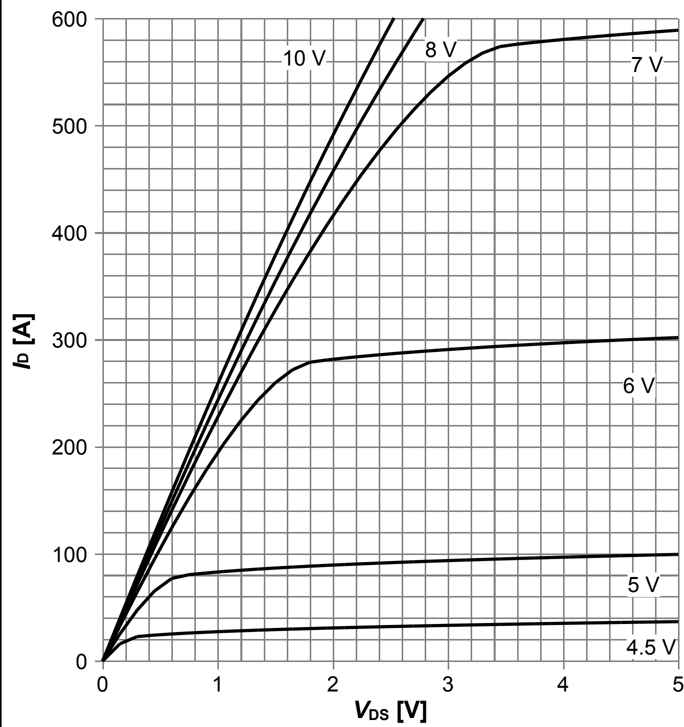
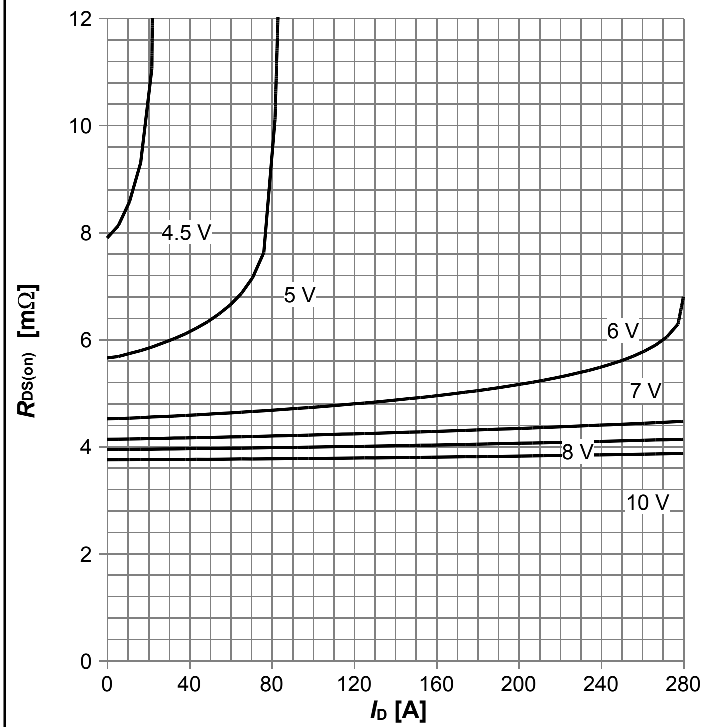
IPB043N10NF2S

Diagram 5: Typ. output characteristics



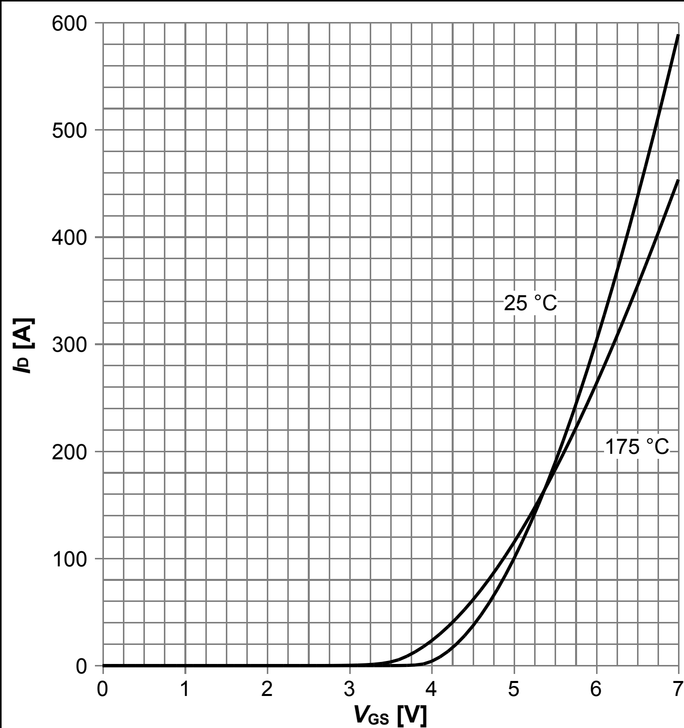
I_D=f(V_{DS}), T_j=25 °C; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



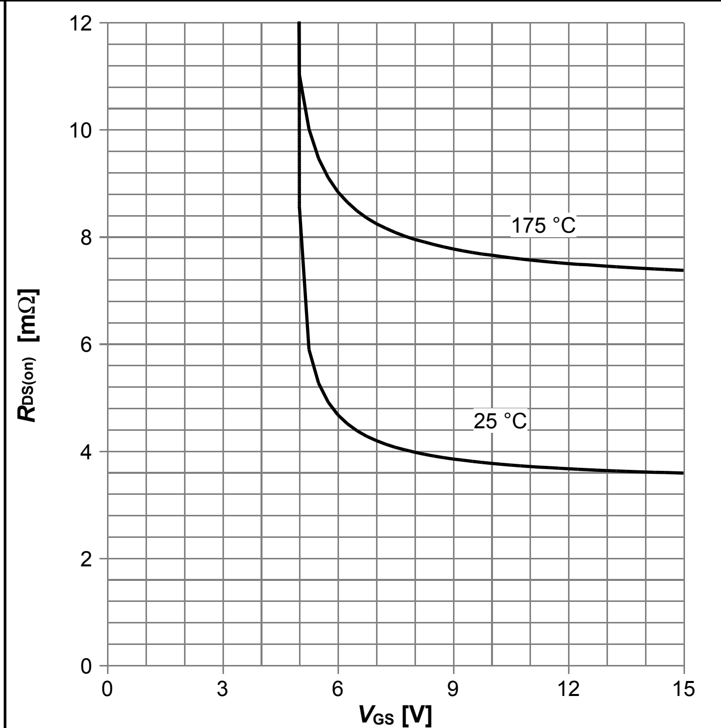
$R_{DS(on)}$=f(I_D), T_j=25 °C; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



I_D=f(V_{GS}), $|V_{DS}|$>2$|I_D|R_{DS(on)max}$; parameter: T_j

Diagram 8: Typ. drain-source on resistance



$R_{DS(on)}$=f(V_{GS}), I_D=80 A; parameter: T_j

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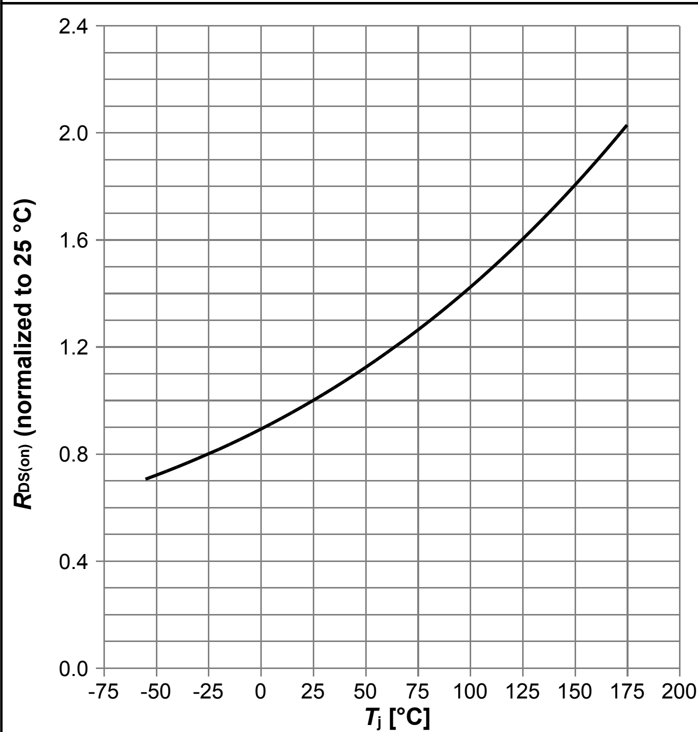
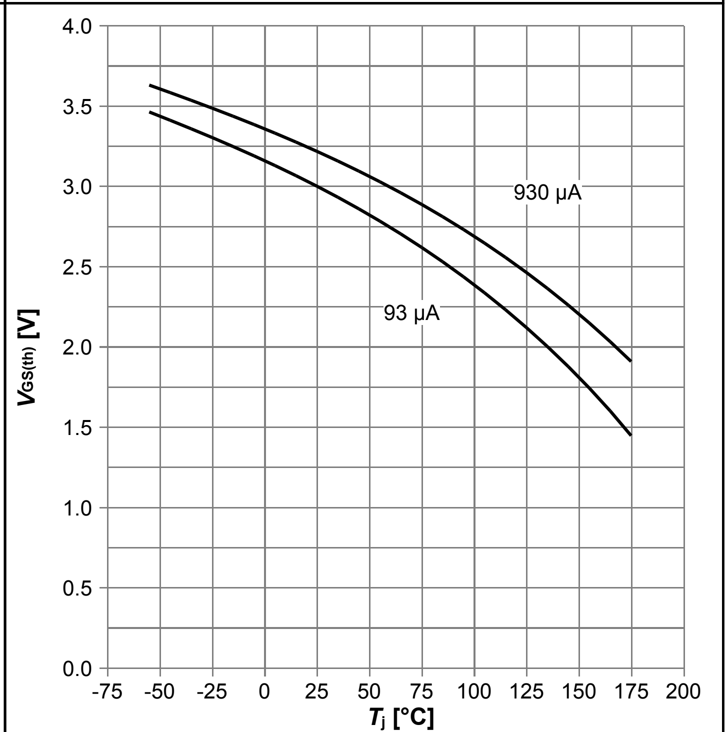
Diagram 9: Normalized drain-source on resistance



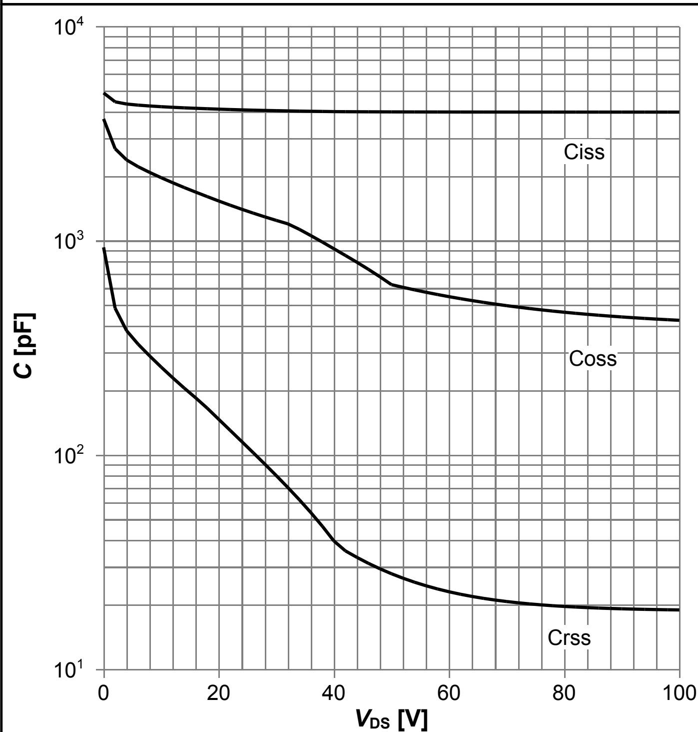
$R_{DS(on)}$=f(T_j), I_D=80 A, V_{GS}=10 V

Diagram 10: Typ. gate threshold voltage



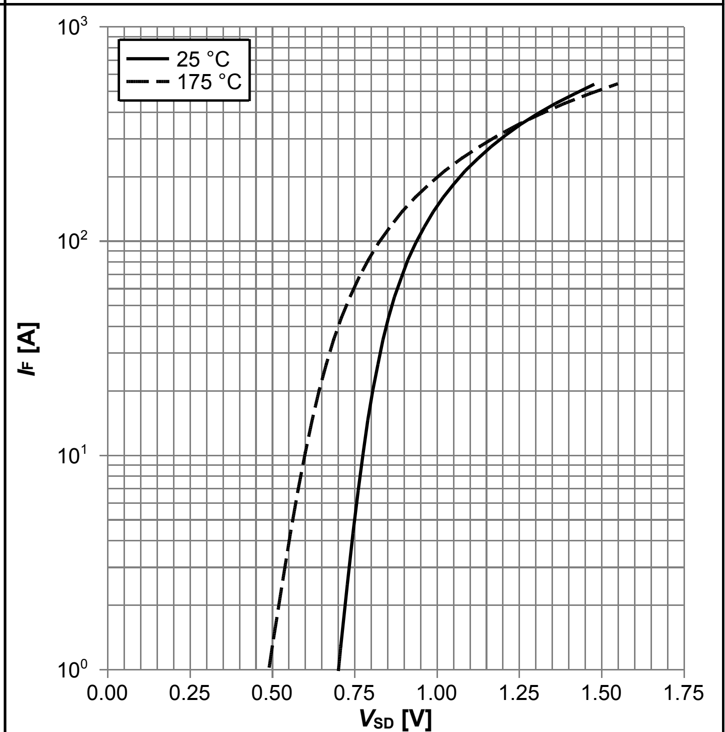
$V_{GS(th)}$=f(T_j), V_{GS}=V_{DS}; parameter: I_D

Diagram 11: Typ. capacitances



C=f(V_{DS}); V_{GS}=0 V; f=1 MHz

Diagram 12: Typ. forward characteristics of reverse diode



I_F=f(V_{SD}); parameter: T_j

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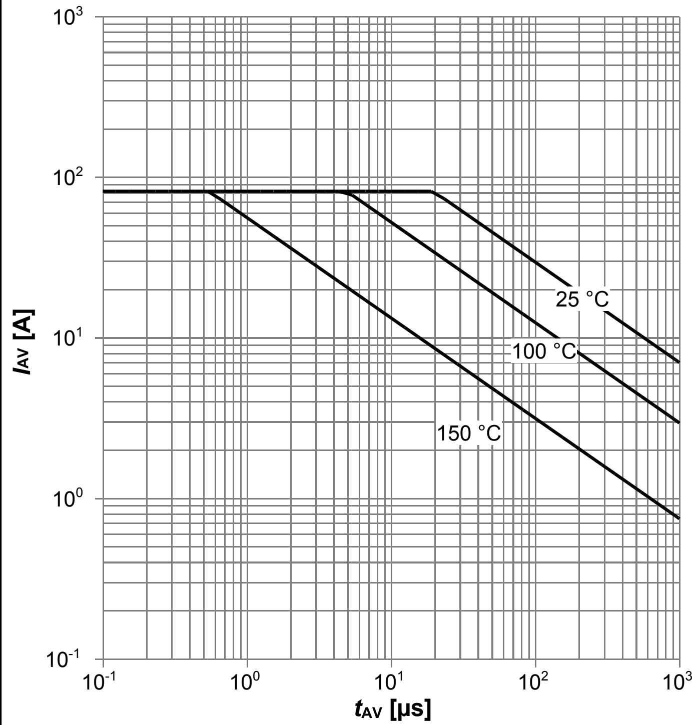
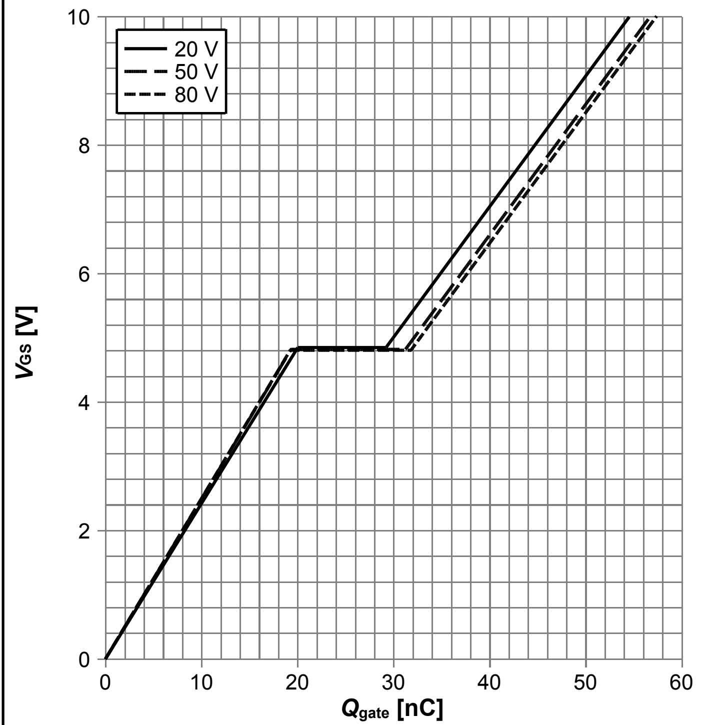
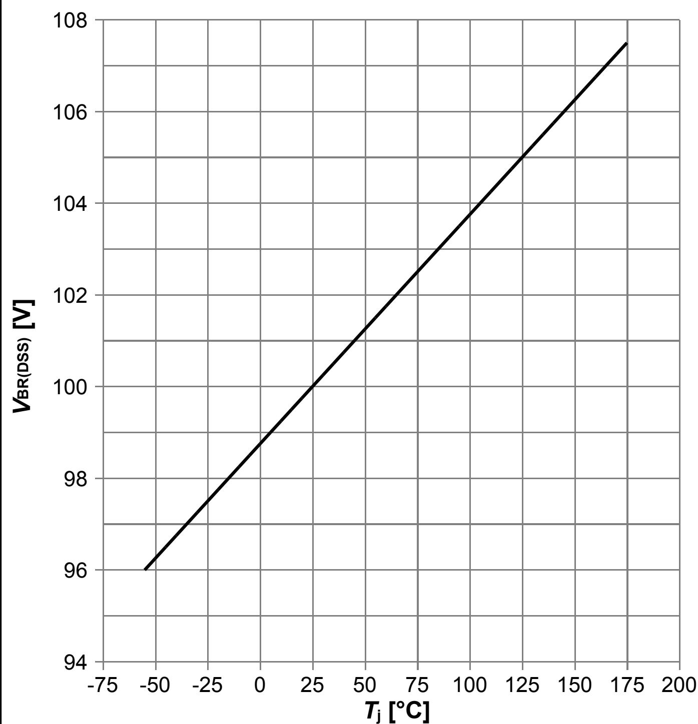
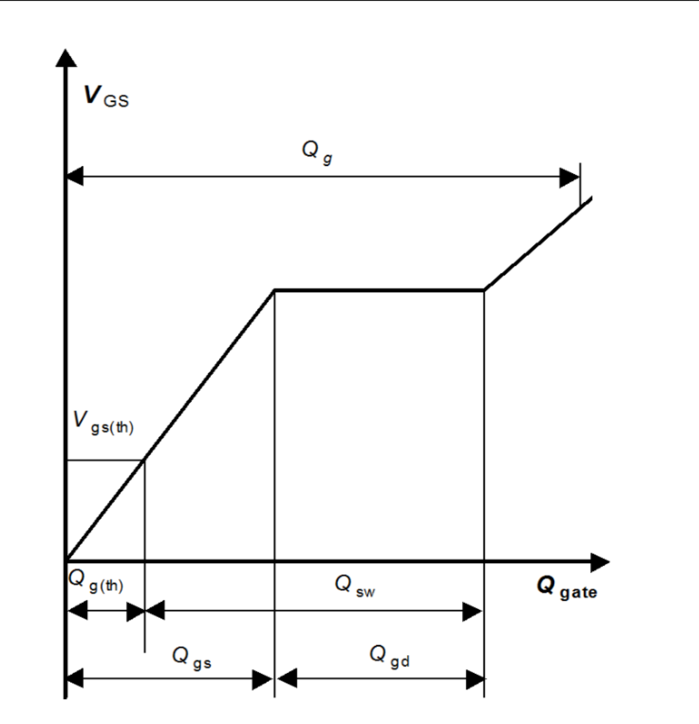
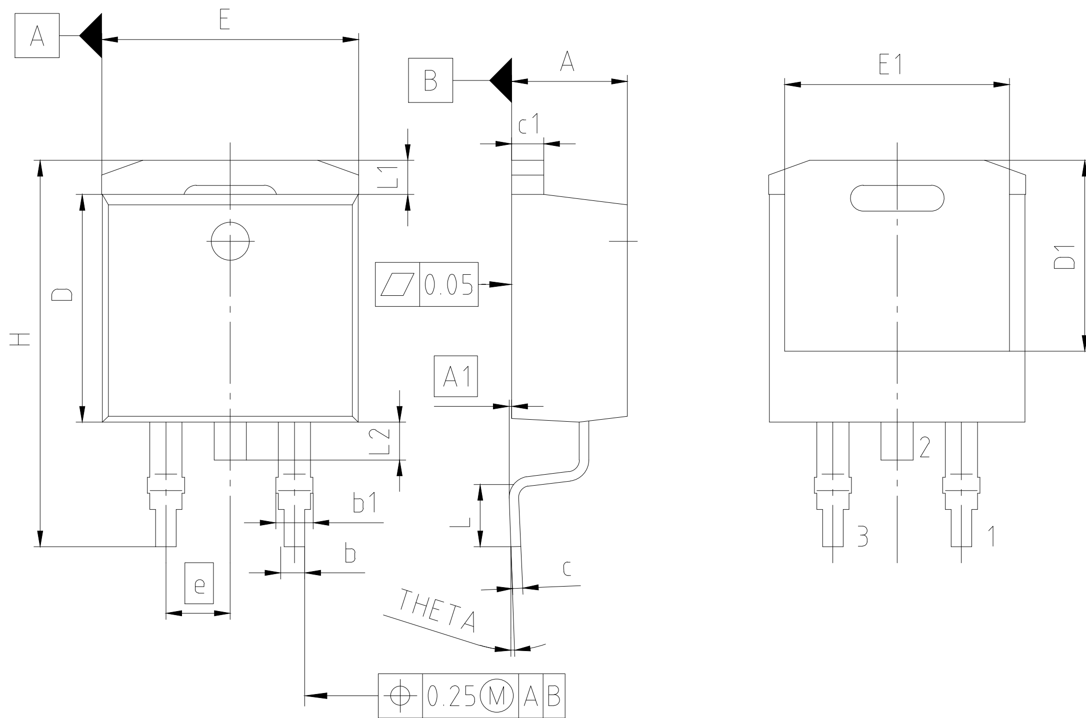
Diagram 13: Avalanche characteristics	Diagram 14: Typ. gate charge
	
I_{AS}=f(t_{AV}); R_{GS}=25 Ω; parameter: $T_{j,start}$	V_{GS}=f(Q_{gate}), I_D=80 A pulsed, T_j=25 °C; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage	Diagram Gate charge waveforms
	
$V_{BR(DSS)}$=f(T_j); I_D=1 mA	

5 Package Outlines



PACKAGE - GROUP NUMBER:	PG-TO263-3-U02	
DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	4.06	4.83
A1	0.00	0.25
b	0.51	1.00
b1	1.07	1.78
c	0.30	0.73
c1	1.14	1.65
D	8.38	9.65
D1	6.60	7.50
E	9.65	10.67
E1	6.22	8.70
e	2.54	
N	3	
H	14.60	15.88
L	1.52	2.60
L1	1.05	1.68
L2	1.35	1.78
THETA	-9.00°	8.00°

PG-TO263-3-10: OPTIONAL
5:1

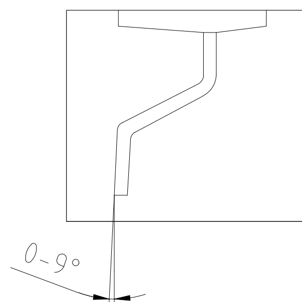


Figure 1 Outline PG-TO263-3, dimensions in mm

Revision History

IPB043N10NF2S

Revision: 2022-09-23, Rev. 2.0

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2022-09-23	Release of final version

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